



### **IXTQ80N28T Information**

Part Number IXTQ80N28T Manufacturer IXYS

Category

Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

MOSFET N-CH 280V 80A TO-3P **Description** 

TO-3P-3, SC-65-3 **Package** 

For the pricing/inventory/lead time, please contact

Website: https://www.heisener.com E-mail: salesdept@heisener.com



Request a Quote

# **Certified Quality**

For Reference Only

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## **IXTQ80N28T Specifications**

Manufacturer Part Number         IXTQ80N28T           Manufacturer         IXYS           Category         Discrete Semiconductor Products           Transistors - FETs, MOSFETs - Single           Package         TO-3P-3, SC-65-3           Series         -           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         280V           Current - Continuous Drain (Id) @ 25°C         80A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         5V @ ImA           Gate Charge (Qg) (Max) @ Vgs         115nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         5000pF @ 25V           Vgs (Max)         ±30V           FET Feature         -           Power Dissipation (Max)         500W (Tc)           Rds On (Max) @ Id, Vgs         49 mOhm @ 500mA, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-3P           Package / Case         TO-3P-3, SC-65-3           Report errors?		
Category  Discrete Semiconductor Products  Transistors - FETs, MOSFETs - Single  Package  TO-3P-3, SC-65-3  Series  - FET Type  N-Channel  Technology  MOSFET (Metal Oxide)  Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  BOA (Tc)  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  Joackage / Case  TO-3P-3, SC-65-3  TO-3P-3, SC-65-3	Manufacturer Part Number	IXTQ80N28T
Package         TO-3P-3, SC-65-3           Series         -           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         280V           Current - Continuous Drain (Id) @ 25°C         80A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         5V @ ImA           Gate Charge (Qg) (Max) @ Vgs         115nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         5000pF @ 25V           Vgs (Max)         ±30V           FET Feature         -           Power Dissipation (Max)         500W (Tc)           Rds On (Max) @ Id, Vgs         49 mOhm @ 500mA, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-3P           Package / Case         TO-3P-3, SC-65-3	Manufacturer	IXYS
Package         TO-3P-3, SC-65-3           Series         -           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         280V           Current - Continuous Drain (Id) @ 25°C         80A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         5V @ 1mA           Gate Charge (Qg) (Max) @ Vgs         115nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         5000pF @ 25V           Vgs (Max)         ±30V           FET Feature         -           Power Dissipation (Max)         500W (Tc)           Rds On (Max) @ Id, Vgs         49 mOhm @ 500mA, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-3P           Package / Case         TO-3P-3, SC-65-3	Category	Discrete Semiconductor Products
Series         -           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         280V           Current - Continuous Drain (Id) @ 25°C         80A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         5V @ 1mA           Gate Charge (Qg) (Max) @ Vgs         115nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         5000pF @ 25V           Vgs (Max)         ±30V           FET Feature         -           Power Dissipation (Max)         500W (Tc)           Rds On (Max) @ Id, Vgs         49 mOhm @ 500mA, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-3P           Package / Case         TO-3P-3, SC-65-3		Transistors - FETs, MOSFETs - Single
FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 280V Current - Continuous Drain (Id) @ 25°C 80A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 1mA Gate Charge (Qg) (Max) @ Vgs 115nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 5000pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 500W (Tc) Rds On (Max) @ Id, Vgs 49 mOhm @ 500mA, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-3P Package / Case To-3P-3, SC-65-3	Package	TO-3P-3, SC-65-3
Technology  Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  80A (Tc)  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Package / Case  MOSFET (Metal Oxide)  80A (Tc)  80B (10V  80D (F @ 25V  80A (TC)  80B (10V  80D (F @ 10V  80D (F @ 25V  80B (10V  80D (F @ 10V  80D (F @	Series	-
Drain to Source Voltage (Vdss)280VCurrent - Continuous Drain (Id) @ 25°C80A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 1mAGate Charge (Qg) (Max) @ Vgs115nC @ 10VInput Capacitance (Ciss) (Max) @ Vds5000pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)500W (Tc)Rds On (Max) @ Id, Vgs49 mOhm @ 500mA, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-3PPackage / CaseTO-3P-3, SC-65-3	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Sty @ 1mA  Gate Charge (Qg) (Max) @ Vgs  115nC @ 10V  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  ### ### #### #######################	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Sty @ 1mA  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  49 mOhm @ 500mA, 10V  Operating Temperature  Supplier Device Package  Package / Case  TO-3P-3, SC-65-3	Drain to Source Voltage (Vdss)	280V
Vgs(th) (Max) @ Id 5V @ 1mA  Gate Charge (Qg) (Max) @ Vgs 115nC @ 10V  Input Capacitance (Ciss) (Max) @ Vds 5000pF @ 25V  Vgs (Max) ±30V  FET Feature -  Power Dissipation (Max) 500W (Tc)  Rds On (Max) @ Id, Vgs 49 mOhm @ 500mA, 10V  Operating Temperature -55°C ~ 150°C (TJ)  Mounting Type Through Hole  Supplier Device Package TO-3P  Package / Case TO-3P-3, SC-65-3	Current - Continuous Drain (Id) @ 25°C	80A (Tc)
Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  5000pF @ 25V  Vgs (Max)  ±30V  FET Feature  - Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  49 mOhm @ 500mA, 10V  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-3P  Package / Case  TO-3P-3, SC-65-3	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  ET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-3P  Package / Case  TO-3P-3, SC-65-3	Vgs(th) (Max) @ Id	5V @ 1mA
Vgs (Max)±30VFET Feature-Power Dissipation (Max)500W (Tc)Rds On (Max) @ Id, Vgs49 mOhm @ 500mA, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-3PPackage / CaseTO-3P-3, SC-65-3	Gate Charge (Qg) (Max) @ Vgs	115nC @ 10V
FET Feature - FET Feature - S00W (Tc)  Rds On (Max) @ Id, Vgs	Input Capacitance (Ciss) (Max) @ Vds	5000pF @ 25V
Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  49 mOhm @ 500mA, 10V  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-3P  Package / Case  TO-3P-3, SC-65-3	Vgs (Max)	±30V
Rds On (Max) @ Id, Vgs49 mOhm @ 500mA, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-3PPackage / CaseTO-3P-3, SC-65-3	FET Feature	-
Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-3P  Package / Case  TO-3P-3, SC-65-3	Power Dissipation (Max)	500W (Tc)
Mounting Type Through Hole Supplier Device Package TO-3P Package / Case TO-3P-3, SC-65-3	Rds On (Max) @ Id, Vgs	49 mOhm @ 500mA, 10V
Supplier Device Package TO-3P Package / Case TO-3P-3, SC-65-3	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-3P-3, SC-65-3	Mounting Type	Through Hole
	Supplier Device Package	TO-3P
Report errors?	Package / Case	TO-3P-3, SC-65-3
		Report errors?

### **IXTQ80N28T Guarantees**



#### **Quality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

### **IXTQ80N28T Payment Methods**









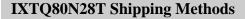
























If you have any question about IXTQ80N28T, please do not hesitate to contact us!

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